

Silicon Diode

BYVB32-100

Fast Efficient Rectifier

100V / 18A

DATASHEET

from

www.web-bcs.com

OEM – General Semiconductor

Source: General Semiconductor Databook 1998

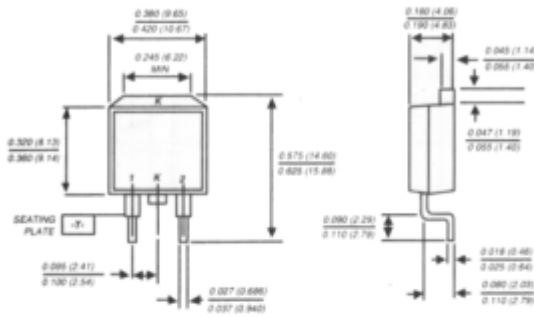
NEW PRODUCT NEW PRODUCT NEW PRODUCT

BYVB32-50 THRU BYVB32-200

FAST EFFICIENT PLASTIC RECTIFIER

Reverse Voltage - 50 to 150 Volts Forward Current - 18.0 Amperes

TO-263AB



Dimensions in inches and (millimeters)

FEATURES

- ◆ Plastic package has Underwriters Laboratory Flammability Classification 94V-0
- ◆ Dual rectifier construction, positive centertap
- ◆ Glass passivated chip junctions
- ◆ Low power loss
- ◆ Low forward voltage, high current capability
- ◆ High surge capability
- ◆ Superfast recovery time for high efficiency
- ◆ High temperature soldering in accordance with CECC 802 / Reflow guaranteed



MECHANICAL DATA

Case: JEDEC TO-263AB molded plastic body
Terminals: Plated leads solderable per MIL-STD-750, Method 2026
Polarity: As marked
Mounting Position: Any
Weight: 0.08 ounce, 2.24 grams

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

	SYMBOLS	BYVB32-50	BYVB32-100	BYVB32-150	BYVB32-200	UNITS
Maximum repetitive peak reverse voltage	VRRM	50	100	150	200	Volts
Maximum RMS voltage	VRMS	35	70	105	140	Volts
Maximum DC blocking voltage	VDC	50	100	150	200	Volts
Maximum average forward rectified current at T _C =120°C	I(AV)	18.0				Amps
Peak forward surge current 10ms single half sine-wave superimposed at at T _J =150°C	IFSM	150.0				Amps
Maximum instantaneous forward voltage per leg at: I _F =20A, I _F =5.0A, T _J =100°C	V _F	1.15 0.85				Volts
Maximum DC reverse current at rated DC blocking voltage T _J =25°C T _J =100°C	I _R	10.0 600.0				μA
Maximum reverse recovery time per leg (NOTE 1)	t _{rr}	35.0				ns
Typical junction capacitance (NOTE 2)	C _J	45.0				pF
Maximum thermal resistance per leg (NOTE 3)	R _{θJC}	3.0				°C/W
Operating and storage temperature range	T _J , T _{STG}	-65 to +150				°C

NOTES:

- (1) Reverse recovery test conditions: I_F=1A V_R=30V, di/dt=100A/μs, I_{rr}=10% I_{sm}
- (2) Measured at 1.0 MHz and applied reverse voltage of 4.0 Volts
- (3) Thermal resistance from junction to case per leg mounted on heatsink

RATINGS AND CHARACTERISTIC CURVES BYVB32-50 THRU BYVB32-200

